

MBR20A100CT

Low Vf Schottky Barrier Rectifiers



Voltage: 100 Volts

Current: 20 Amperes

Package: TO-220AB

Features

- NH'S Low Vf Schottky Barrier Chip Technology
- Super Low Forward Voltage Drop For High Efficiency
- Low Power Loss For High Reliability
- High Frequency Switching Speed

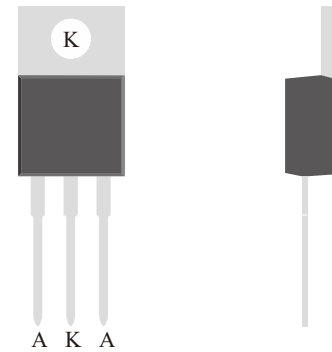
Mechanical Data

- **Case:** Molded With UL-94 ClassV-0 Recognized, RoHS-Compliant
- **Polarity:** Look At The Diagram And Polarity On The Right
- **Terminals:** Tin Plated Leads,Solderable Per J-STD-002 And JESD22-B102

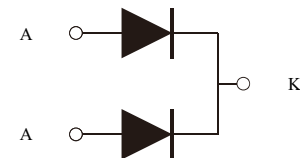
Typical Applications

- Switch Mode Power Supplies (SMPS)
- Fast Chargers
- LED Driver And Monitor Lighting
- Automotive Electronics And Charging Posts

Diagram:



Polarity:



Single Phase,Half Wave,60Hz,Resistive Or Inductive Load.For Capacitive Load,Derate Current By 20%

Maximum Ratings (Ta=25°C Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Ratings	Unit
Maximum Repetitive Peak Reverse Voltage		V_{RRM}	100	V
Maximum RMS Voltage		V_{RMS}	70	V
Maximum DC Blocking Voltage		V_{DC}	100	V
Maximum Average Forward Rectified Current	Per Diode Total device	$I_{F(AV)}$	10 20	A
Peak Forward Surge Current Per Diode	8.3ms Single Half Sine-wave Superimposed On Rate Load	I_{FSM}	120	A
Current Squared Time Per Diode	$t < 8.3ms$	I^2t	59.8	A ² sec
Maximum Mounting Torque	M3 screw	T_{MM}	1.1	N.m

Electrical Characteristics (Ta=25°C Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Ratings			Unit
			Min.	Typ.	Max.	
Instantaneous Forward Voltage Per Diode	Ta=25°C Ta=100°C If= 10.0 A	V_F	-- --	0.73 0.67	0.77 0.73	V
Maximum DC Reverse Current at Rated DC Blocking Voltage	Ta=25°C , $V_R=V_{RRM}$ Ta=100°C , $V_R=V_{RRM}*80\%$	I_{RRM}	-- --	7 1	60 12	uA mA
Typical Junction Capacitance Per Diode	4 V,1MHz	C_J	--	550	--	pF

Thermal Characteristics (Ta=25°C Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Ratings			Unit
Operating Junction Temperature Range		T _J	-55	to	150	°C
Storage Temperature Range		T _{STD}	-55	to	150	
Thermal Resistance Junction To Ambient With Steady-State	Still Air Environment With Ta=25 °C	R _{θJA}	62.5			°C/W
Thermal Resistance Junction-Case With Steady-State	Device Mounted On 75mm x 45mm x 2.5mm Alu. Heat.	R _{θJC}	2.0			

Notes: 1.Pulse Test: 300 Us Pulse Width,1% Duty Cycle

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Typical Characteristics Curves

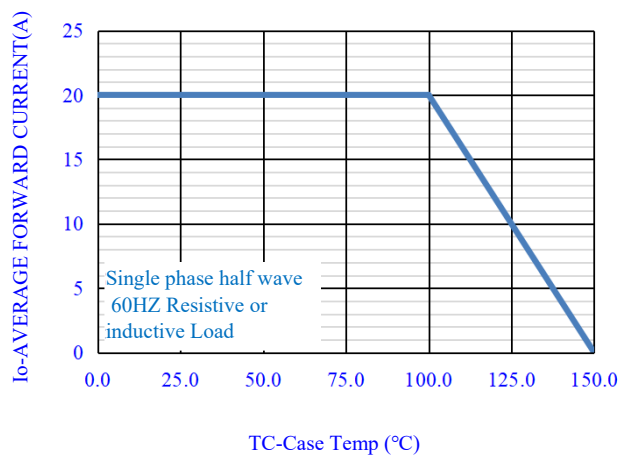


Fig.1-FORWARD CURRENT DERATING CURVE

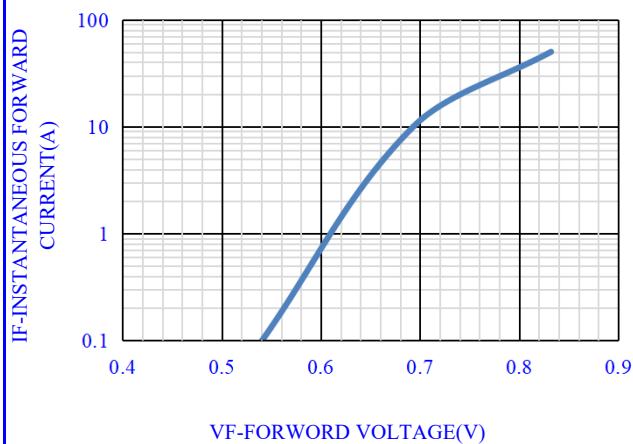


Fig.2- TYPICAL INSTANTANEOUS FORWARD

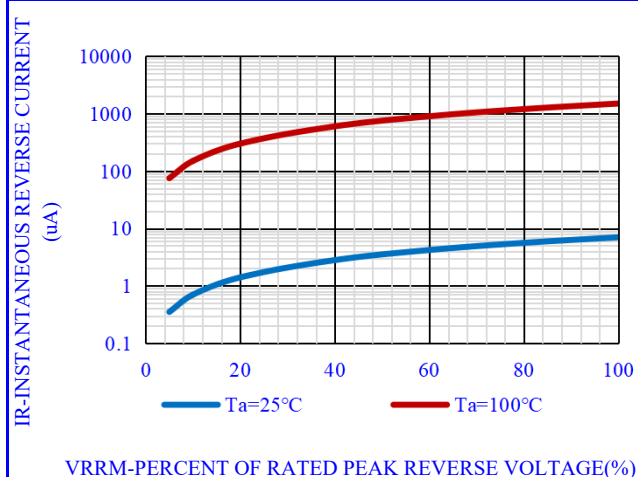


Fig.3- TYPICAL REVERSE CHARACTERISTICS

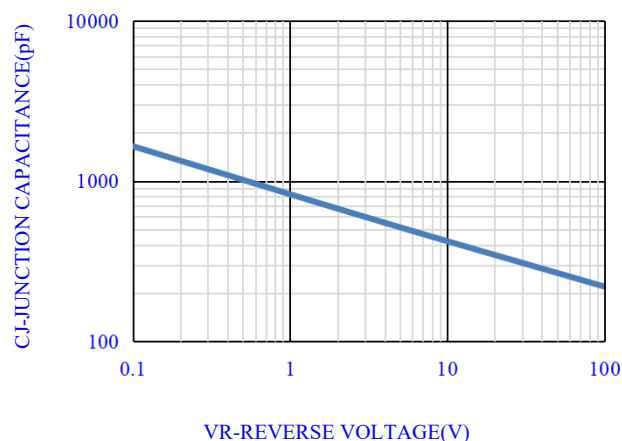


Fig.4- TYPICAL JUNCTION CAPACITANCE

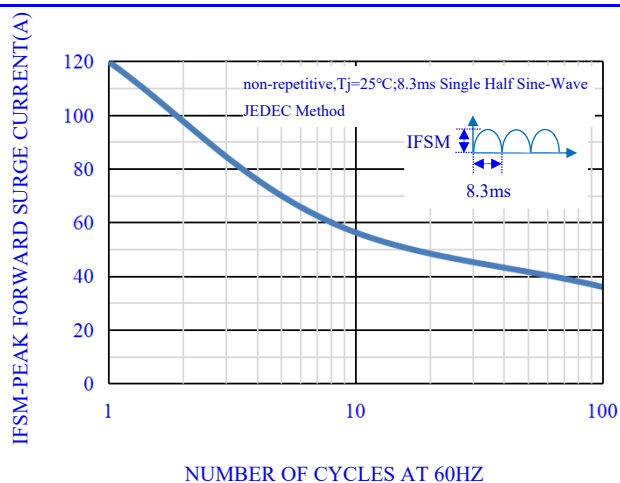


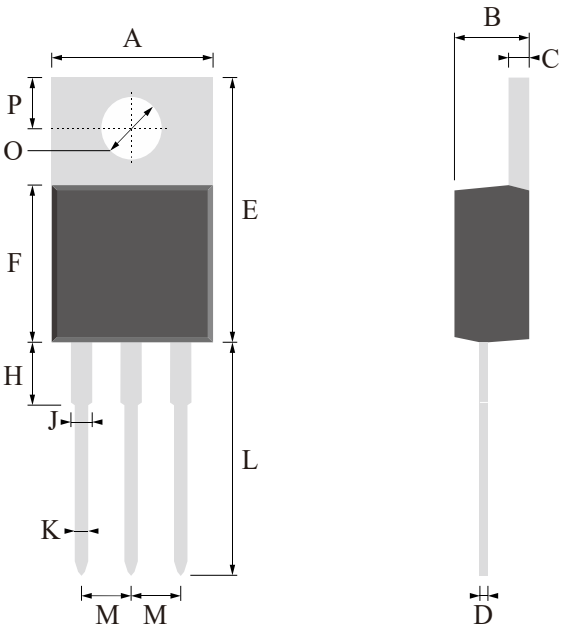
Fig.5-MAX. NON-REPETITIVE SURGE CURRENT

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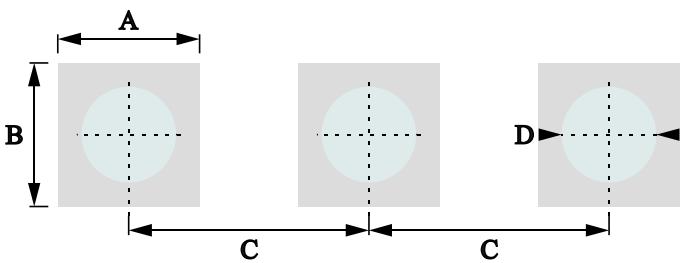
OUTLINE DRAWINGS



TO-220AB

OUTLINE DIMENSIONS						
Dim.	Milimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.25	-	10.75	0.3642	-	0.4232
B	1.10	-	1.65	0.0433	-	0.0650
C	4.15	-	4.95	0.1634	-	0.1949
D	0.25	-	0.65	0.0098	-	0.0256
E	14.50	-	16.70	0.5709	-	0.6575
F	8.40	-	9.95	0.3307	-	0.3917
L	12.15	-	14.30	0.4783	-	0.5630
H	3.00	-	3.80	0.1181	-	0.1496
J	1.05	-	1.60	0.0413	-	0.0630
K	0.65	-	0.95	0.0256	-	0.0374
M	2.10	-	2.90	0.0827	-	0.1142
O	3.20	-	4.10	0.1260	-	0.1614
P	2.45	-	3.10	0.0965	-	0.1220

RECOMMEDND LAYOUT DRAWINGS



TO-220AB

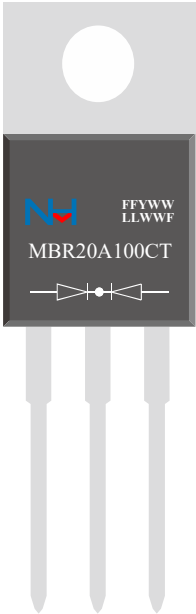
OUTLINE DIMENSIONS						
Dim.	Milimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	-	1.60	-	-	0.0630	-
B	-	1.60	-	-	0.0630	-
C	-	2.54	-	-	0.1000	-
D	-	1.00	-	-	0.0394	-

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MARKING



MARKING INSTRUCTION

NH=Niuhan Trademark
FF=Product Line Code,According To Actual Changes
YWW=Date Code,According To Actual Changes
LLWWF=Inernal Code,According To Actual Changes
MBR20A100CT=Model

PACKING INFORMATION

Package Type	Package Code	Product Weight Approx(g/Pcs)	Package Method	Quantity (Pcs/Min. Pack.)	Quantity (Pcs/Inner Box)	Quantity (Pcs/Carton)
TO-220AB	P1	2.057	Tube	50	1000	5000

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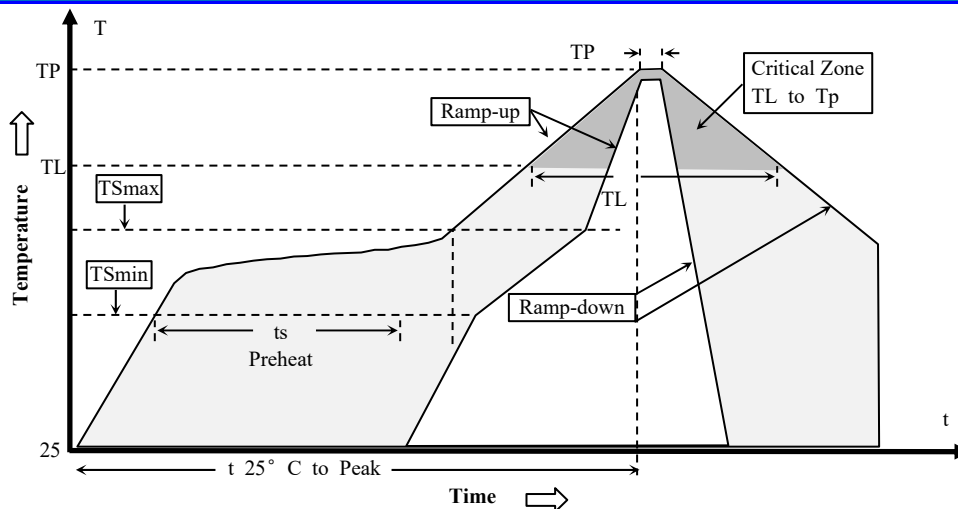
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Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
Preheat -Temperature Min(TS min) -Temperature Max(TS max) -Time(ts min to ts max)	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
Time maintained above: -Temperature (TL) - Time (tL)	183°C 60-150 seconds	217°C 60-150 seconds
Peak Temperature(TP)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

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